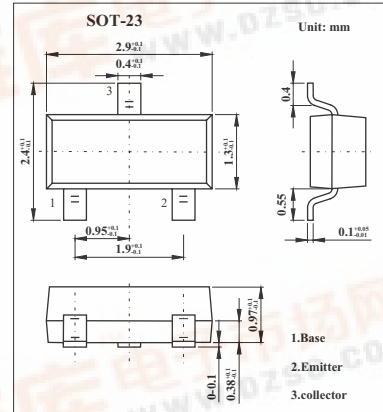


SMD Type Transistors

Silicon NPN Epitaxial
2SC4209

Features



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	80	V
Collector-emitter voltage	V _{CEO}	80	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	300	mA
Base current	I _B	60	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 50 V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0			0.1	μA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 5mA, I _B = 0	80			V
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 50 mA	70		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 200 mA, I _B = 10 mA			0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 5 mA	0.55		0.8	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 10 mA		100		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		10		pF

hFE Classification

Marking	C	
	O	Y
Rank	70~140	120~240

